Supplementary material for

An insight of p-type to n-type conductivity conversion in oxygenion-implanted ultrananocrystalline diamond films by impedance spectroscopy

Hui Xu1, 2, Haitao Ye2, a), David Coathup2, Ivona Z. Mitrovic3, Ayendra D. Weerakkody3, Xiaojun Hu1, b)

1. *College of Materials Science and Engineering, Zhejiang University of Technology, Hangzhou, China*
2. *School of Engineering and Applied Science, Aston University, Birmingham B4 7ET, United Kingdom*
3. *Department of Electrical Engineering and Electronics, University of Liverpool, Liverpool L69 3GJ, United Kingdom*

a) Electronic email: h.ye@aston.ac.uk

b) Electronic email: [huxj@zjut.edu.cn](mailto:huxj@zjut.edu.cn)

S1: The complex impedance of UNCD films fitted by a double resistance-capacitance (RC) parallel and a resistance (R) model in series.

, (S1)

, (S2)

. (S3)

When plotted in the complex plane, versus takes the form of two semicircles in which the contributions of diamond grains and grain boundaries are easily identified, hence the electrical conduction paths of the bulk material can be studied separately.

Figure S1. Temperature dependence of resistance from I-V measurement of samples 900-A and O12900. Linear curve fitting from 20-100 oC shows activation energy values are 0.04 and 0.11 eV for samples 900-A and O12900, respectively.

